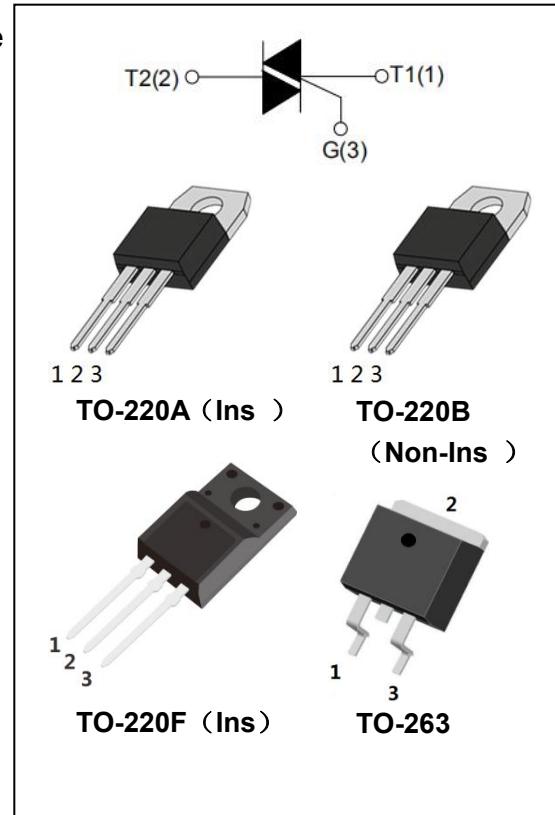


## DESCRIPTION:

With high ability to withstand the shock loading of Large current, BTA20/BTB20 series triacs provide high dv/dt rate with strong resistance to electromagnetic interface.

With high commutation performances, 3 quadrants products especially recommended for use on inductive load. From all three terminals to external heatsink, BTA20 (TO-220A) provides a rated insulation voltage of 2500 V<sub>RMS</sub> complying with UL standards (File ref: E516503).



## MAIN FEATURES:

symbol	value	unit
I <sub>T(RMS)</sub>	20	A
V <sub>DRM/V<sub>RRM</sub></sub>	600/800/1200	V

## ABSOLUTE MAXIMUM RATINGS:

Parameter	Symbol	Value	Unit
Storage junction temperature range	T <sub>stg</sub>	-40~150	°C
Operating junction temperature range	T <sub>j</sub>	-40~125	°C
Repetitive peak off-state voltage (T <sub>j</sub> =25°C)	V <sub>DRM</sub>	600/800/1200	V
Repetitive peak reverse voltage (T <sub>j</sub> =25°C)	V <sub>RRM</sub>	600/800/1200	V
RMS on-state current	I <sub>T(RMS)</sub>	20	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I <sub>TSM</sub>	200	A
I <sup>2</sup> t value for fusing (t <sub>p</sub> =10ms)	I <sup>2</sup> t	200	A <sup>2</sup> s
Critical rate of rise of on-state current(I <sub>G</sub> =2×I <sub>GT</sub> )	di/dt	100	A/μs
Peak gate current	I <sub>GM</sub>	4	A
Average gate power dissipation	P <sub>G(AV)</sub>	1	W
Peak gate power	P <sub>GM</sub>	10	W

**ELECTRICAL CHARACTERISTICS (T<sub>j</sub>=25°C unless otherwise specified)**
**3 Quadrants:**

Parameter	Test Condition	Quadrant		Value		Unit
				CW	BW	
I <sub>GT</sub>	V <sub>D</sub> =12V, R <sub>L</sub> =33Ω	I - II - III	MAX	35	50	mA
V <sub>GT</sub>				1.3		V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub>	I - II - III	MIN	0.2		V
I <sub>H</sub>	I <sub>T</sub> =100mA		MAX	50	60	mA
I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	I - III	MAX	60	70	mA
		II		70	90	
dV/dt	V <sub>D</sub> =2/3V <sub>DRM</sub> T <sub>j</sub> =125°C Gate open		MIN	500	1000	V/μs

**4 Quadrants:**

Parameter	Test Condition	Quadrant		Value		Unit
				C	B	
I <sub>GT</sub>	V <sub>D</sub> =12V, R <sub>L</sub> =33Ω	I - II - III	MAX	25	50	mA
		IV		50	70	mA
V <sub>GT</sub>	ALL			1.5		V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub>	ALL	MIN	0.2		V
I <sub>H</sub>	I <sub>T</sub> =100mA		MAX	40	60	mA
I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	I - III - IV	MAX	50	70	mA
		II		70	90	
dV/dt	V <sub>D</sub> =2/3V <sub>DRM</sub> T <sub>j</sub> =125°C Gate open		MIN	200	500	V/μs

## STATIC CHARACTERISTICS

Symbol	Test Condition			Value	Unit
$V_{TM}$	$I_{TM}=28A$	$t_p=380\mu s$	$T_j=25^\circ C$	MAX	1.5 V
$I_{DRM}$	$V_{DRM}=V_{RRM}$	$T_j=25^\circ C$	$T_j=125^\circ C$	MAX	5 $\mu A$
$I_{RRM}$					2 mA

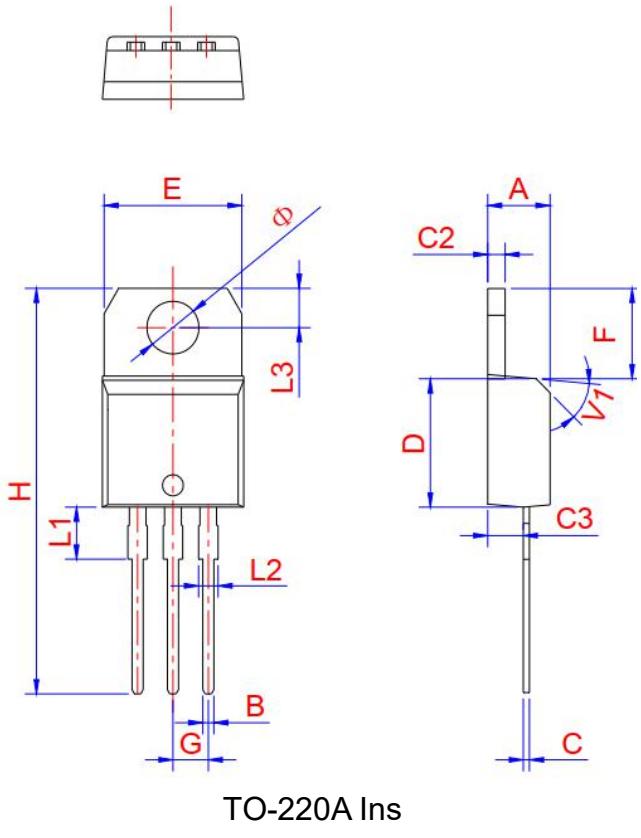
## THERMAL RESISTANCES

Symbol	Test Condition	Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220A(Ins)	1.9
		TO-220B(Non-Ins)	1.1
		TO-220F(Ins)	2.1
		TO-263	2.4

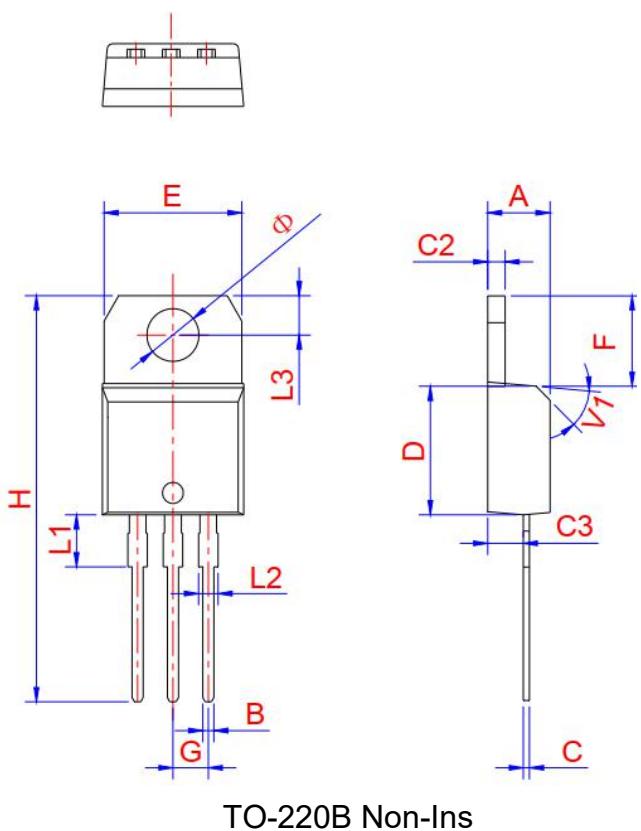
## ORDERING INFORMATION

<u>B</u> <u>T</u> <u>A</u> <u>2 0 - 8 0 0</u> <u>C</u> <u>W</u> Triacs A:Insulated B:Non-Insulated	$I_{T(RMS)}:20A$	$V_{DRM}、V_{RRM}:$ 600: 600V 800: 800V 1200: 1200V	B: $I_{GT1-3}\leq 50mA, I_{GT4}\leq 100mA$ C: $I_{GT1-3}\leq 25mA, I_{GT4}\leq 50mA$ CW: $I_{GT1-3}\leq 35mA$ BW: $I_{GT1-3}\leq 50mA$
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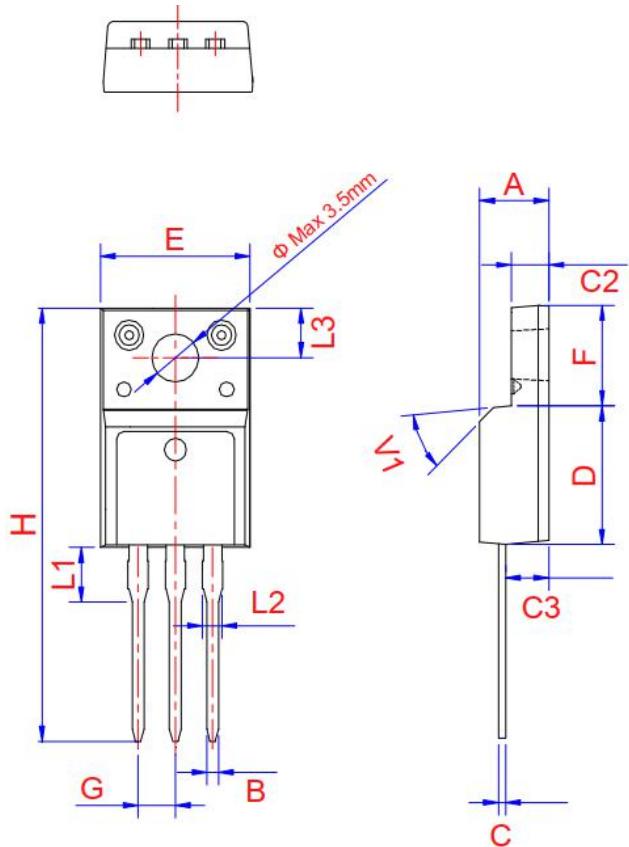
### PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4	4.47	4.6	0.173	0.176	0.181
B	0.61		0.88	0.024		0.035
C	0.46	0.50	0.7	0.018	0.02	0.028
C2	1.21	1.27	1.32	0.048	0.050	0.052
C3	2.4		2.72	0.094		0.107
D	8.6		9.7	0.339		0.382
E	9.8		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.7	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	
Φ	3.7	3.75	3.8	0.145	0.147	0.149

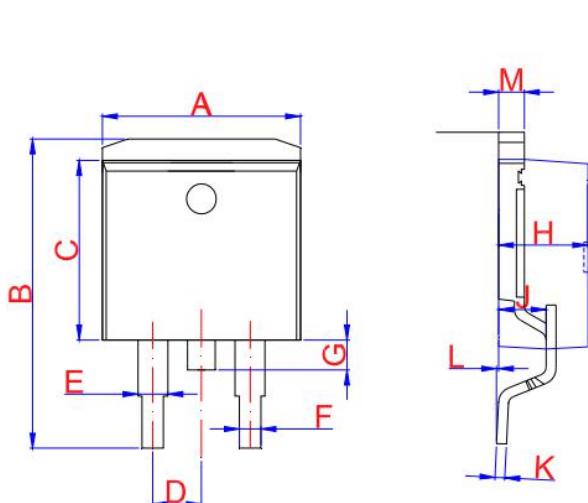


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4	4.47	4.6	0.173	0.176	0.181
B	0.61		0.88	0.024		0.035
C	0.46	0.50	0.7	0.018	0.02	0.028
C2	1.21	1.27	1.32	0.048	0.050	0.052
C3	2.4		2.72	0.094		0.107
D	8.6		9.7	0.339		0.382
E	9.8		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.7	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	
Φ	3.7	3.75	3.8	0.145	0.147	0.149



TO-220F Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.5		4.9	0.177		0.193
B	0.74	0.8	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.6		3	0.102		0.118
D	8.8		9.3	0.346		0.366
E	9.8		10.4	0.386		0.41
F	6.4		6.8	0.252		0.268
G		2.54			0.1	
H	28		29.8	1.102		1.173
L1		3.63			0.148	
L2	1.14		1.7	0.045		0.067
L3	2.65	3.3	0		0.13	0.116
V1		45°			45°	

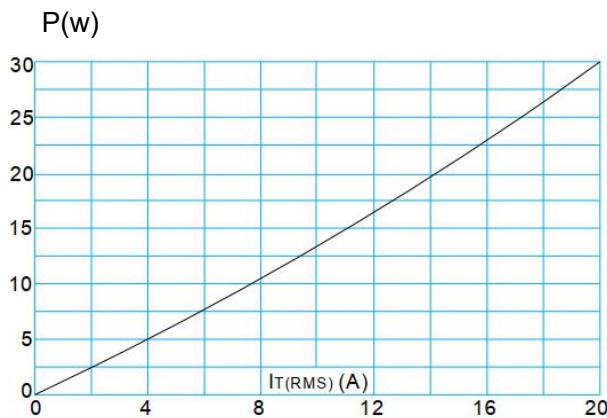


TO-263

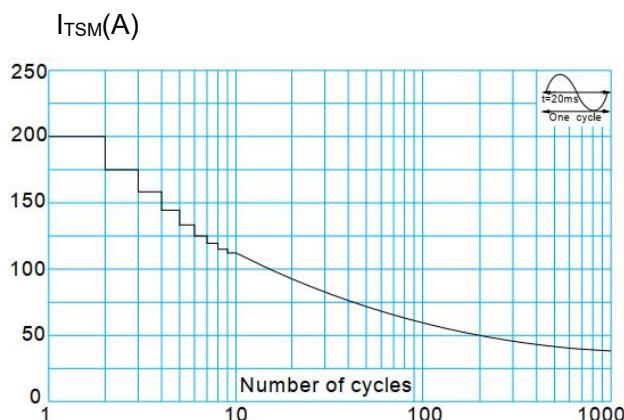
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.9		10.3	0.390		0.406
B	14.7		15.8	0.579		0.622
C	8.5		8.9	0.370		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40	4.60	4.80	0.173	0.181	0.189
J	2.40	2.60	2.80	0.094	0.102	0.110
L	0	0.1	0.25	0	0.004	0.010
M	1.17	1.27	1.37	0.046	0.05	0.054



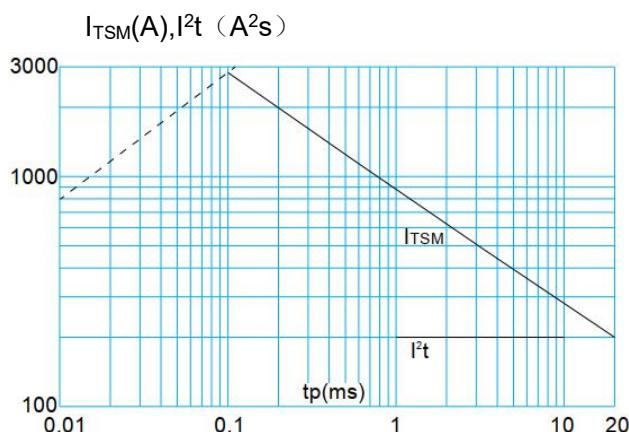
**FIG.1:** Maximum power dissipation versus RMS on-state current



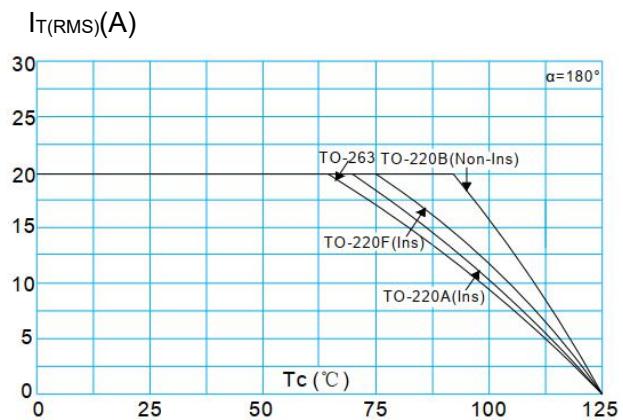
**FIG.3:** Surge peak on-state current versus number of cycles



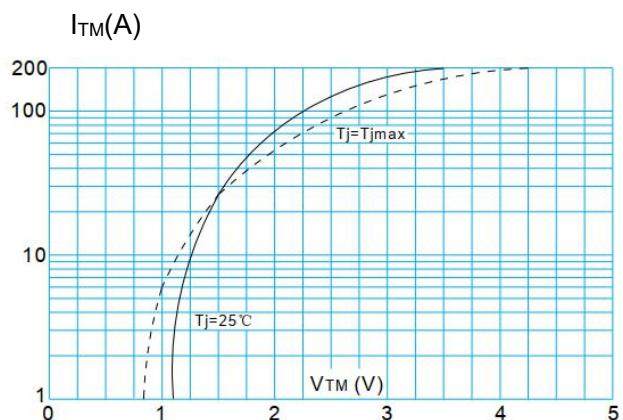
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20 \text{ ms}$ , and corresponding value of  $I^2t$  ( $I - \text{II} - \text{III}: dI/dt < 50 \text{ A}/\mu\text{s}; \text{IV}: dI/dt < 10 \text{ A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics (maximum values)



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

